

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

### LISTING OF THE CLAIMS:

Claims 1-6 (cancelled)

1           7. (original) A semiconductor device comprising:  
2           a first memory cell having a first MIS transistor, a  
3           second MIS transistor, a third MIS transistor and a fourth  
4           MIS transistor, which are of an N channel type;  
5           a second memory cell having a fifth MIS transistor, a  
6           sixth MIS transistor, a seventh MIS transistor and an  
7           eighth MIS transistor, which are of an N channel type,  
8           wherein the gate-insulating film thickness of said  
9           first MIS transistor is smaller than that of said fifth MIS  
10          transistor.

1           8. (original) The semiconductor device according to  
2          claim 7, further comprising:  
3           a ninth MIS transistor in an input/output circuit;  
4           a logic circuit having a tenth MIS transistor,  
5          wherein

6           the gate-insulating film thickness of said ninth MIS  
7 transistor is larger than that of said first MIS  
8 transistor,

9           the gate-insulating film thickness of said tenth MIS  
10 transistor is smaller than that of said fifth MIS  
11 transistor.

1           9. (original) The semiconductor device according to  
2 claim 7, further comprising:

3           an input/output circuit; and  
4           a logic circuit, wherein

5           the gate-insulating film thickness of the MIS  
6 transistor in said logic circuit is equal to that of said  
7 first MIS transistor,

8           the gate-insulating film thickness of the MIS  
9 transistor in said input/output circuit is equal to that of  
10 said fifth MIS transistor,

11           said first memory cell has a ninth MIS transistor and  
12 a tenth MIS transistor, which are of a P channel type,

13           said second memory cell has an eleventh MIS transistor  
14 and a twelfth MIS transistor, which are of a P channel  
15 type,

16           the gates of said third MIS transistor and said fourth  
17 MIS transistor are connected to a wordline, the gate of

18 said first MIS transistor is connected to said fourth MIS  
19 transistor, the drain thereof is connected to said third  
20 MIS transistor, the gate of said second MIS transistor is  
21 connected to said third MIS transistor, and the drain  
22 thereof is connected to said second MIS transistor,  
23 the gates of said seventh MIS transistor and said  
24 eighth MIS transistor are connected to a wordline, the gate  
25 of said fifth MIS transistor is connected to said eighth  
26 MIS transistor, the drain thereof is connected to said  
27 seventh MIS transistor, the gate of said sixth MIS  
28 transistor is connected to said seventh MIS transistor, and  
29 the drain thereof is connected to said eighth MIS  
30 transistor.

1 10. (original) The semiconductor device according to  
2 claim 7, further comprising:

3 a ninth MIS transistor having a source-drain path  
4 between the operating voltage supply point of said first  
5 memory cell and the power line,

6 wherein said ninth MIS transistor is controlled so as  
7 to be in the off state in a first state and to be in the on  
8 state in a second state,

9           before said second state is changed to said first  
10 state, information of said first memory cell is stored into  
11 said second memory cell.

Claims 11-15 (cancelled)